

ABSTRACT OF THE DISCLOSURE (FIG. 2)

"METHOD FOR MANUFACTURING ELECTRODE PLATE FOR
PLASMA PROCESSING DEVICE"

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A method manufactures an electrode plate for a plasma processing device in which a semiconductor wafer is processed to form a highly integrated circuit. The method includes a curing step of heat-curing a liquid thermosetting resin to prepare a resin forming material, one or two backing steps of carbonizing the heat-cured resin forming material by heating under a non-oxidizing atmosphere to prepare a baking material composed of glass-like carbon and a polishing step of polishing one face of the baking material, which is exposed to plasma, to a depth of 20 μm to 1.25 mm.

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